

High Power Density Power Management IC Module with On-Chip Inductors

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ICT for Energy Efficiency

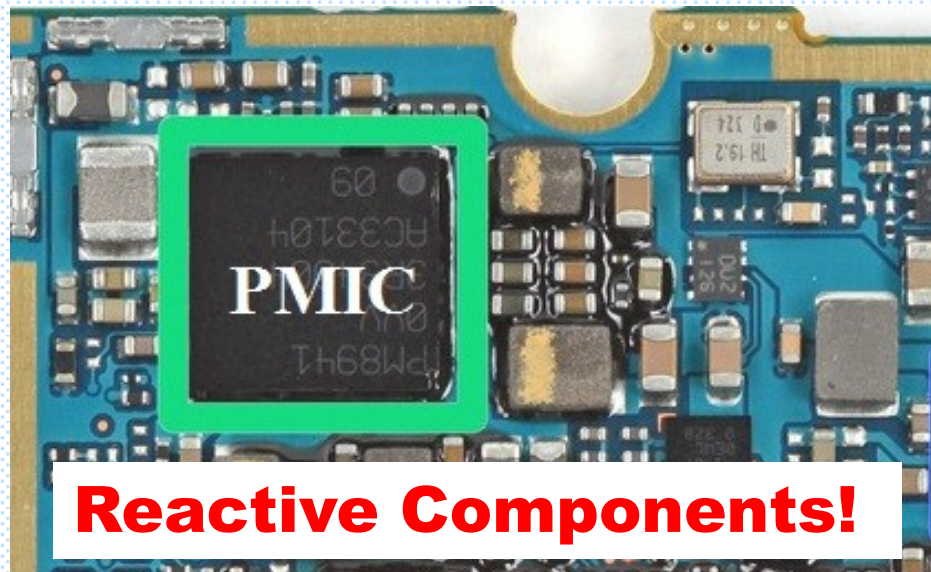
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- ❑ Introduction and Motivation
 - Goal of the collaborative research
- ❑ High density power management architecture
 - Topology and principle of operation
 - Comparison with conventional architecture
- ❑ IC implementation with on-chip inductors
 - High density power management modules
 - Experimental Results
- ❑ Conclusions

- In a conventional power management solution for portable applications:
 - As many as 30+ separate dc-dc power supplies
 - Take up to 80% of overall device volume
 - Reactive components consume most of the volume



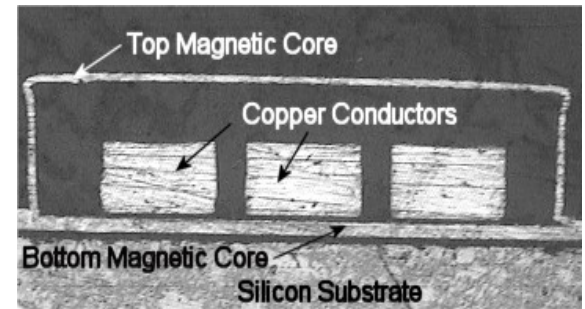
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Nexus 5 Smartphone

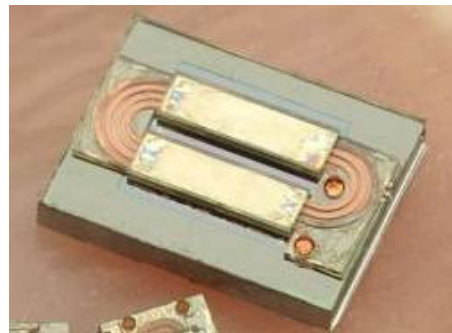


Tyndall Micro-fabricated Magnetics on Silicon

- Electroplated copper windings.
- Thin-film, electroplated magnetic core.
- Design optimization process
 - Focus on efficiency and footprint.
 - Coupled to validated models.
- Race-track shape to achieve:
 - good frequency response
 - high inductance density
 - Low DC resistance
- CMOS-compatible process:
 - Copper coils deposited by electroplating
 - Core consists of thin film of NiFe alloy deposited by electroplating



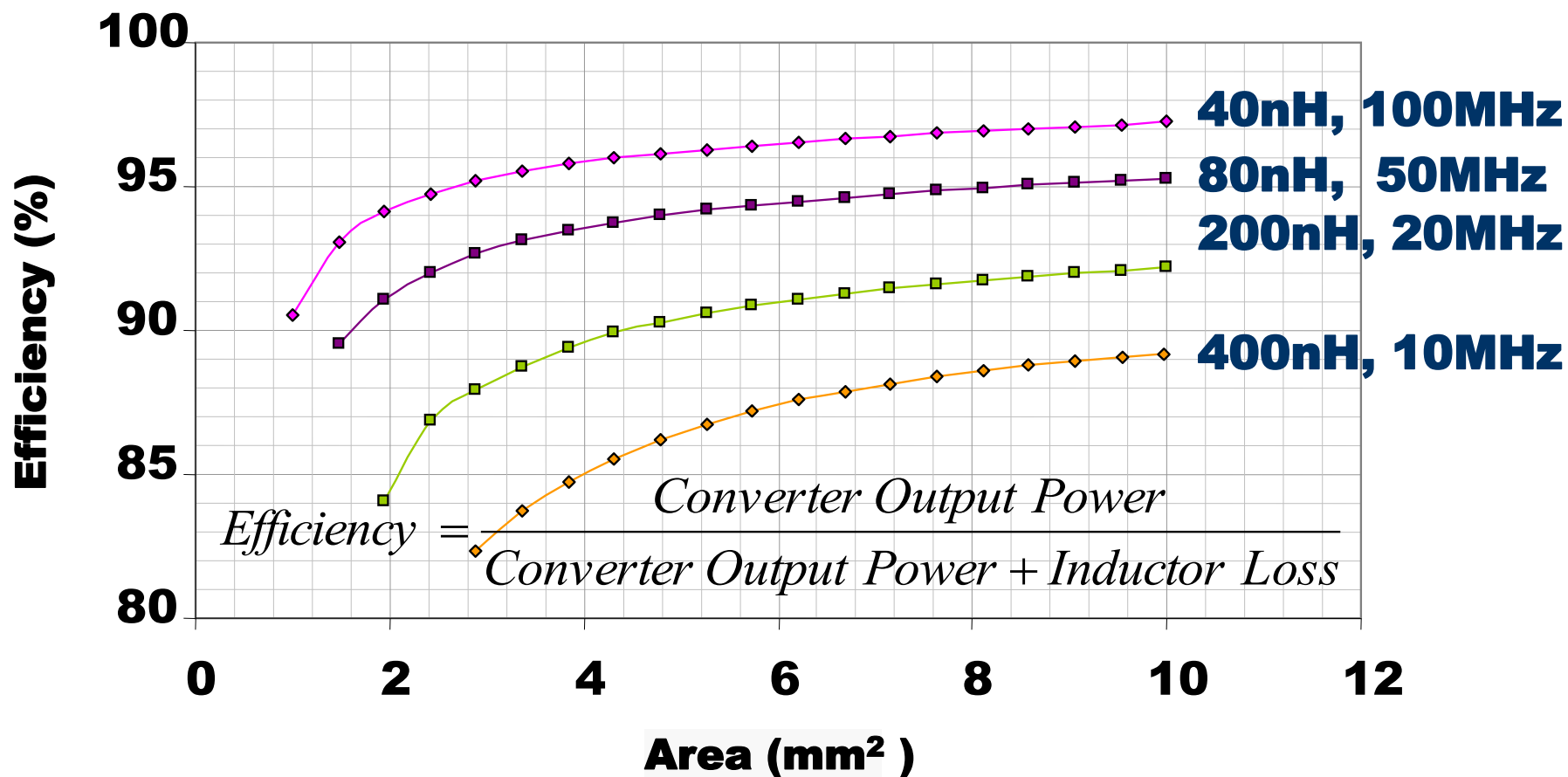
*Cross section
of a micro-inductor*



*Micro-inductors fabricated
on 4 inch Si wafer*

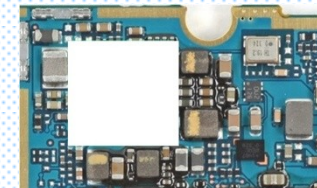
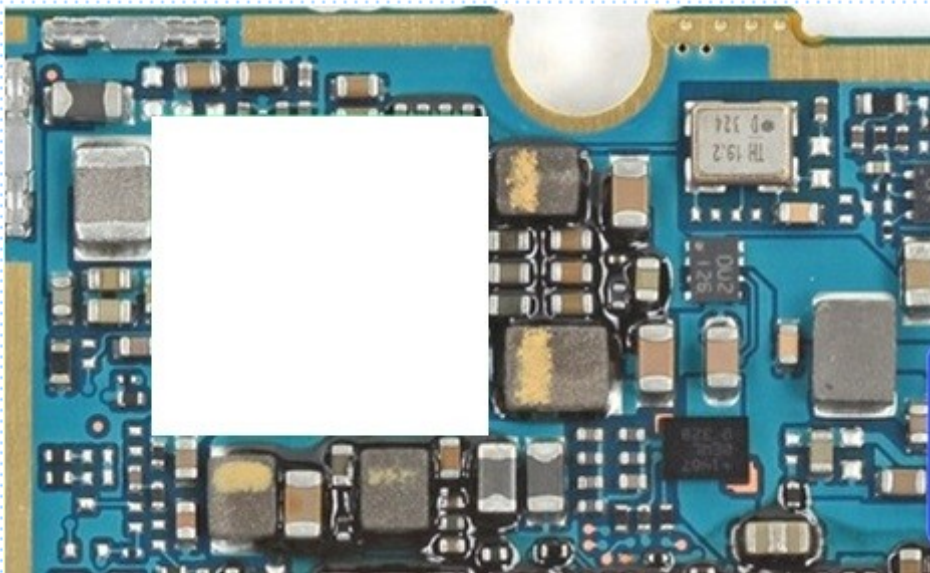


Micro-inductor efficiency increases with frequency multi-parameter optimization at 500mA

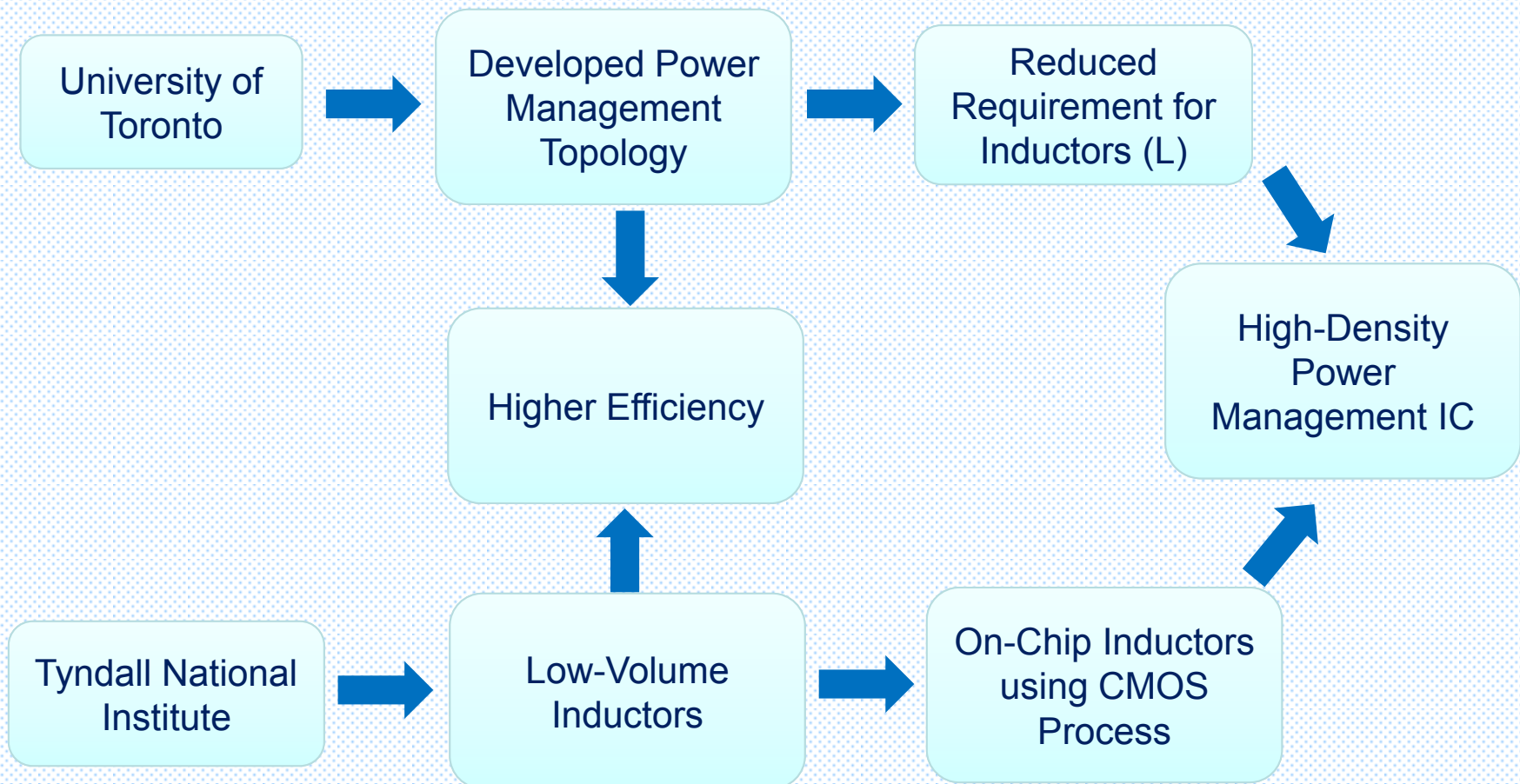


- ❑ Inductors with higher efficiency are smaller in values
 - Require the converter to operate at higher switching frequency
 - Result in significant increase in switching losses

- ❑ To reduce the volume consumed by power management modules by:
 - First, developing new power management architecture
 - Reduce size of inductors
 - Increase the efficiency
 - Second, utilize advanced high efficiency on chip inductors
 - Increase power density

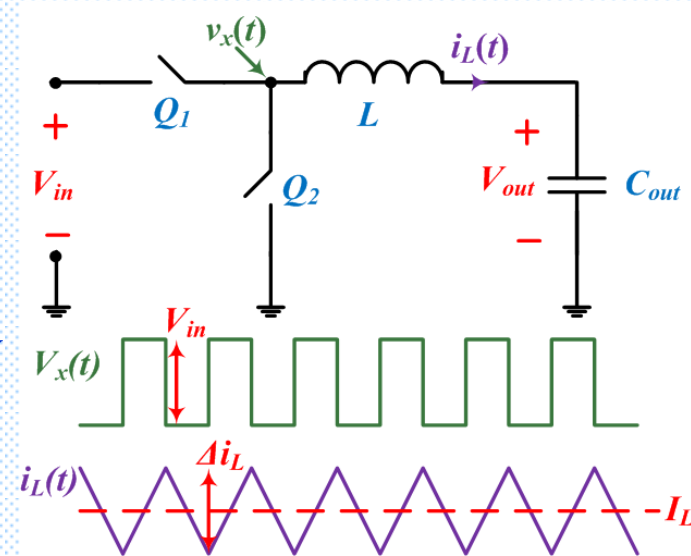


- To reduce the volume consumed by power management modules:

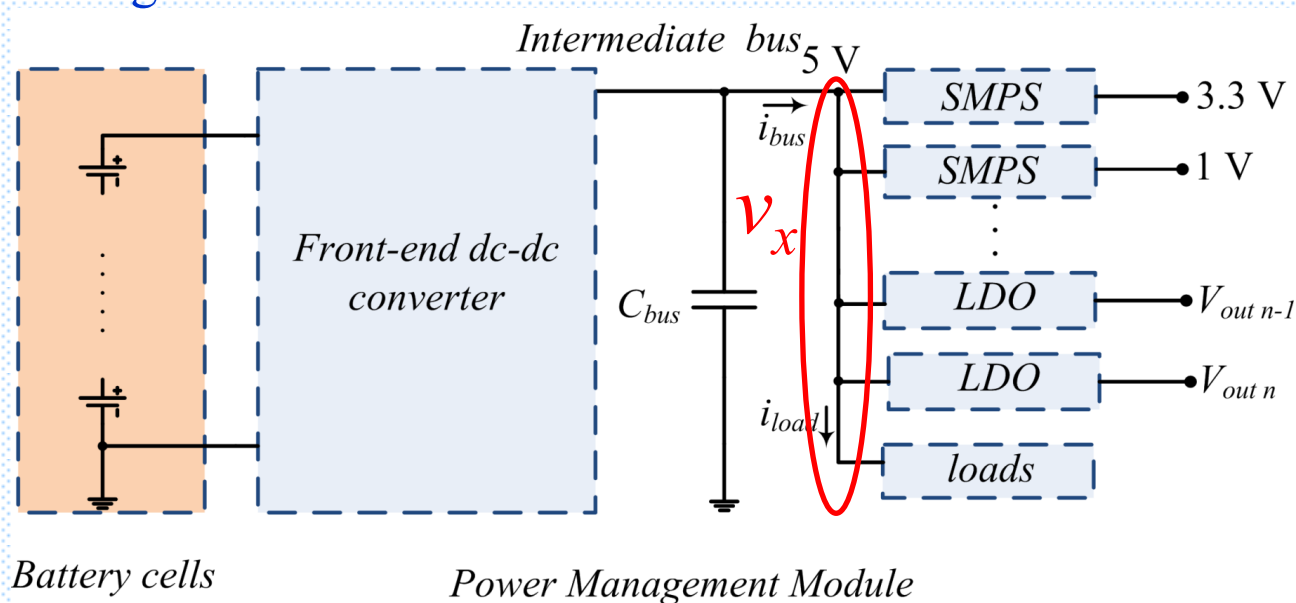


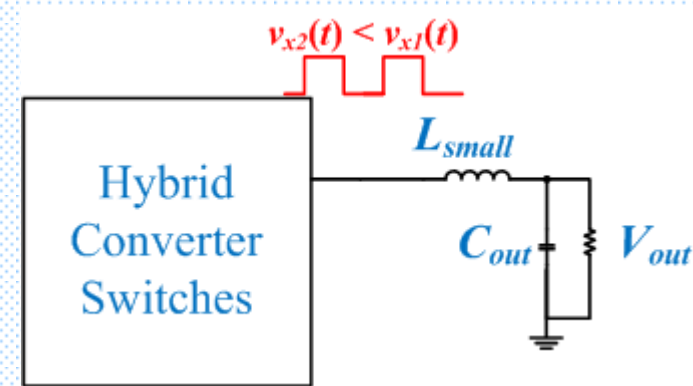
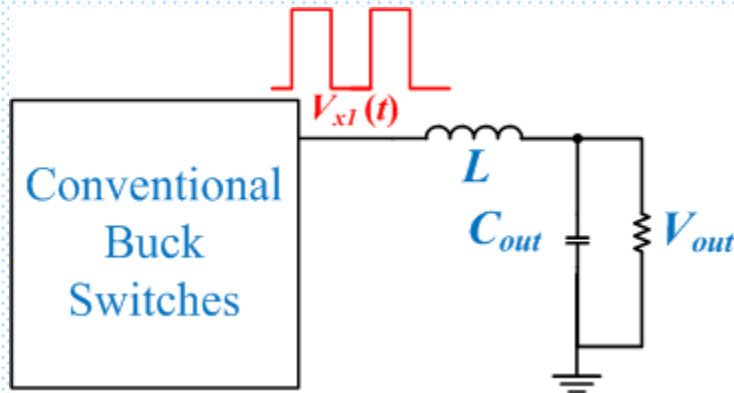
$$\text{Inductor Current Ripple, } \Delta i_L = \frac{(V_{in} - V_{out}) \cdot D}{2 \cdot L \cdot f_{sw}}$$

Increasing switching frequency $\rightarrow$ efficiency penalty



- In a conventional fixed bus voltage based architecture inductors often work with relatively high voltage swings



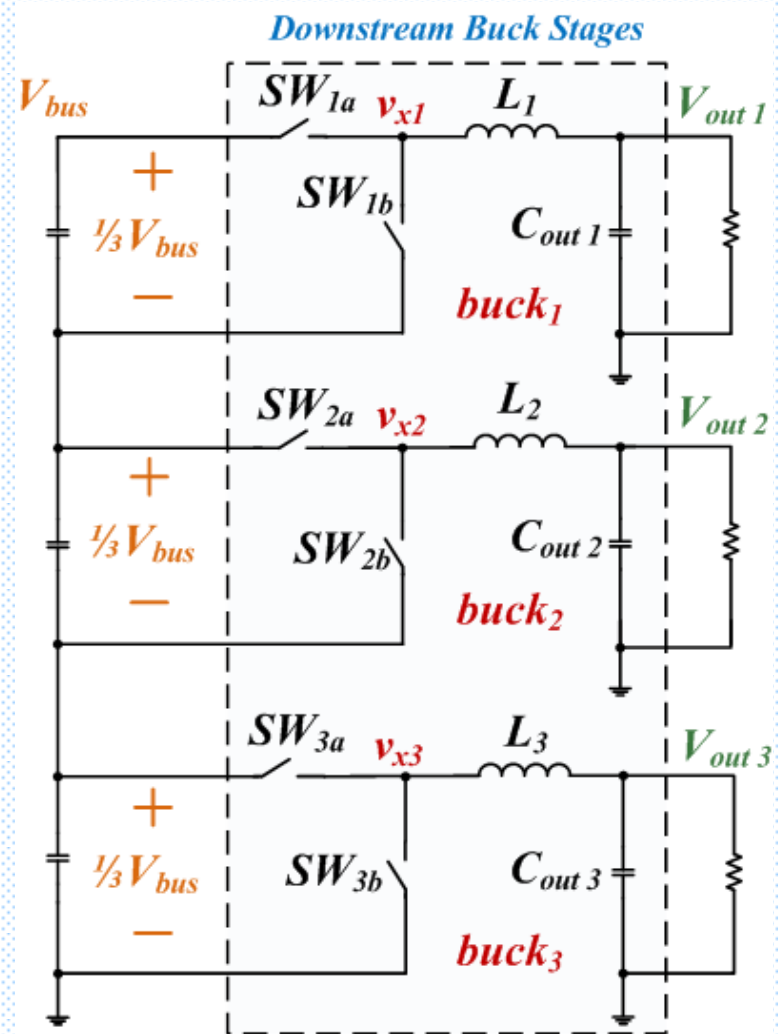


$$\text{Inductor Current Ripple, } \Delta i_L = \frac{(V_{in} - V_{out}) \cdot D}{2 \cdot L \cdot f_{sw}}$$

- ❑ By reducing the voltage swing at the switching node, inductor sizes are reduced without:
 - Significantly increasing switching frequency
 - Paying the price in efficiency penalty
- ❖ Increased efficiency due to reduction of switching losses

Multiple intermediate voltage levels

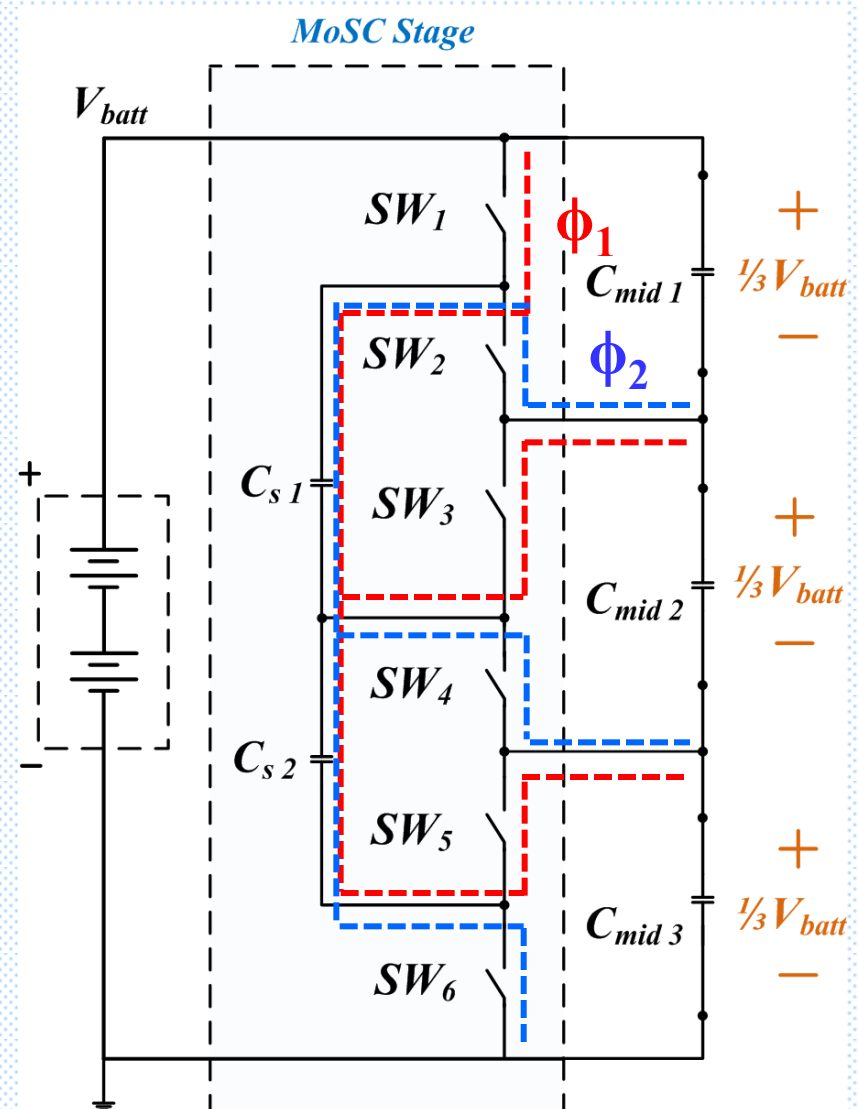
- Reduced voltage swings across inductors reduce the required inductor sizes for same ripple
- Differentially connected buck converters have increased efficiency due to reduced switching losses
- Operating at a higher switching frequency further reduces inductor sizes



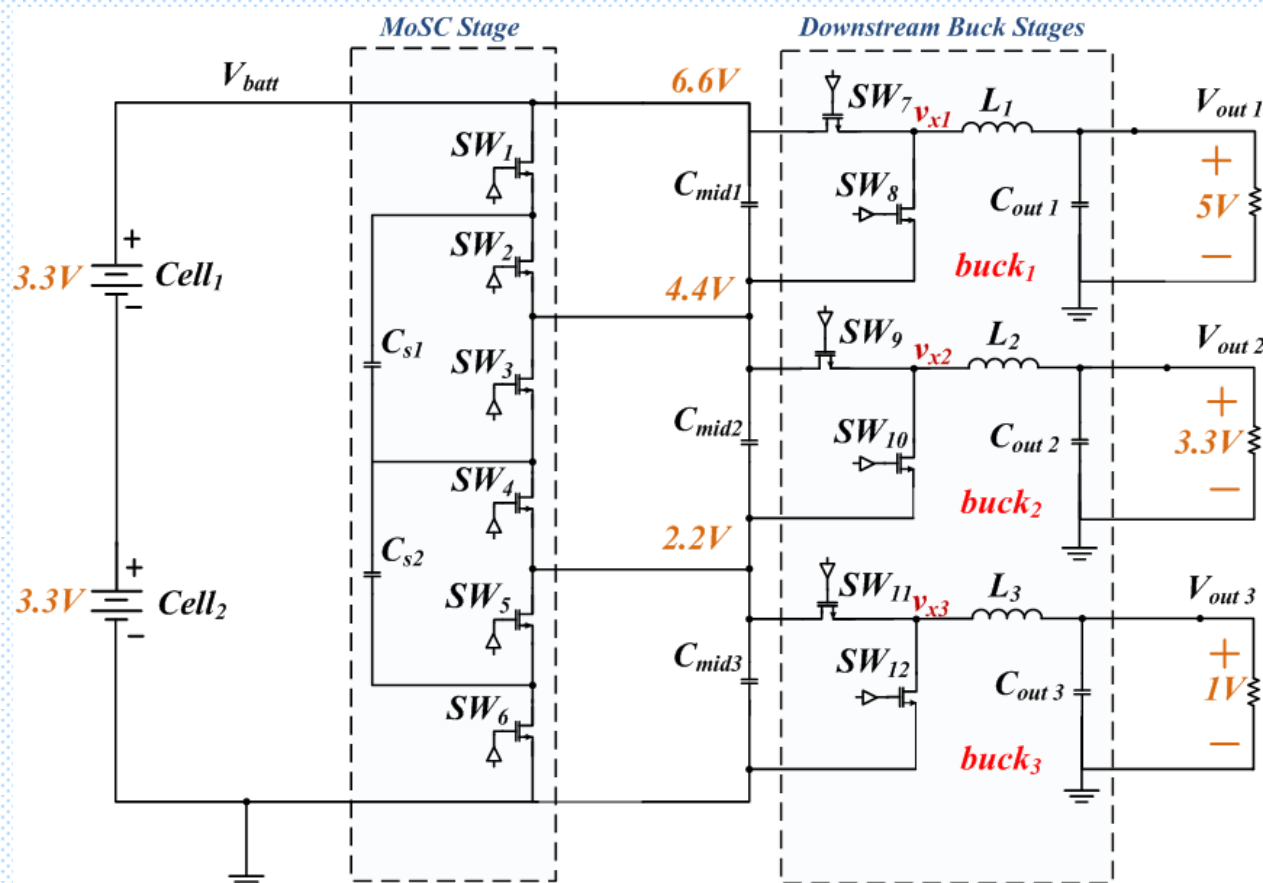
Ahsanuzzaman, S.M.; Blackman, J.; McRae, T.; Prodic, A, "A low-volume power management module for portable applications based on a multi-output switched-capacitor circuit," *Applied Power Electronics Conference and Exposition (APEC), 2013 Twenty-Eighth Annual IEEE* , pp.1473,1479, 17-21 March 2013

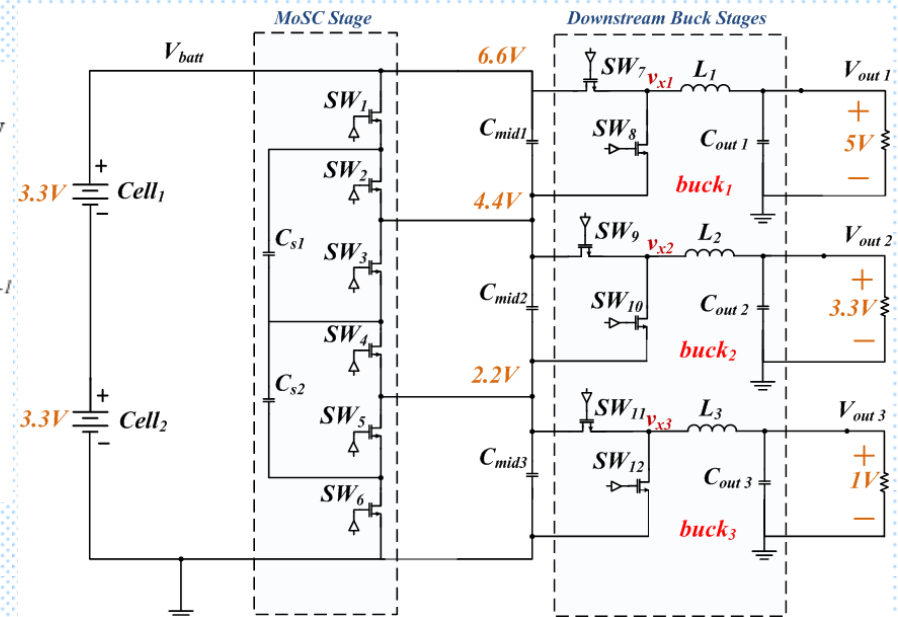
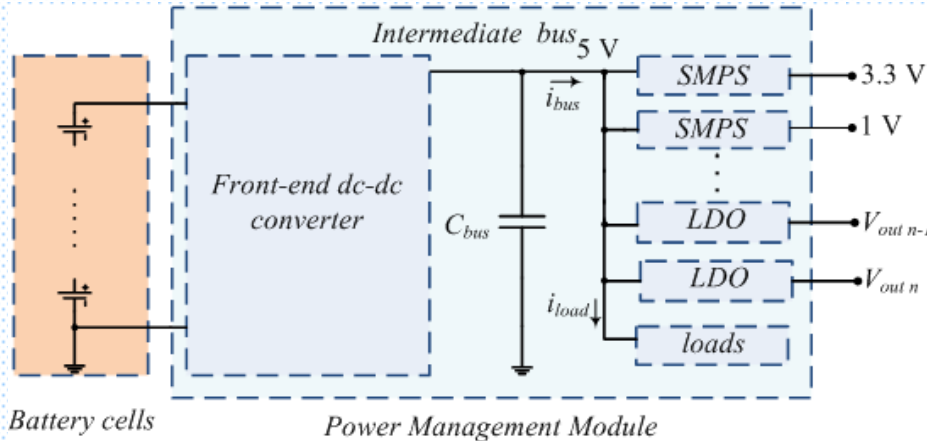
Multi-Output SC Front Stage

- Fixed-ratio switched capacitor circuits show high efficiency
- 2 flying capacitors (C_{s1} and C_{s2}) are used with 6 switches with 50% duty ratio
- Each intermediate capacitor (C_{mid1} , C_{mid2} , C_{mid3}) holds $1/3^{\text{rd}}$ of the battery voltage



- ❑ 1 V output: Digital processors
- ❑ 3.3 V output: analog components (i.e. power amplifiers)
- ❑ 5 V output: USB ports and peripherals

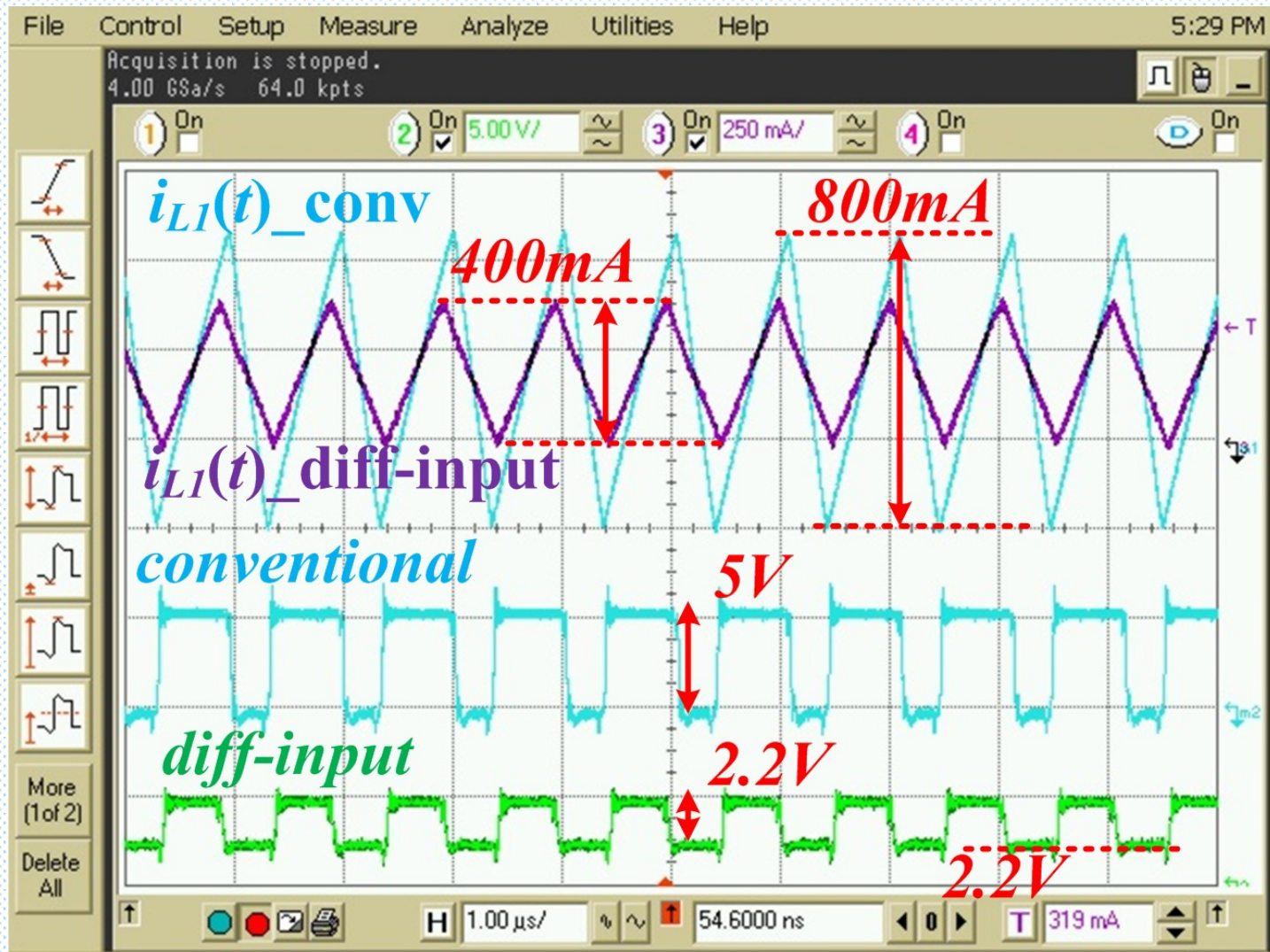




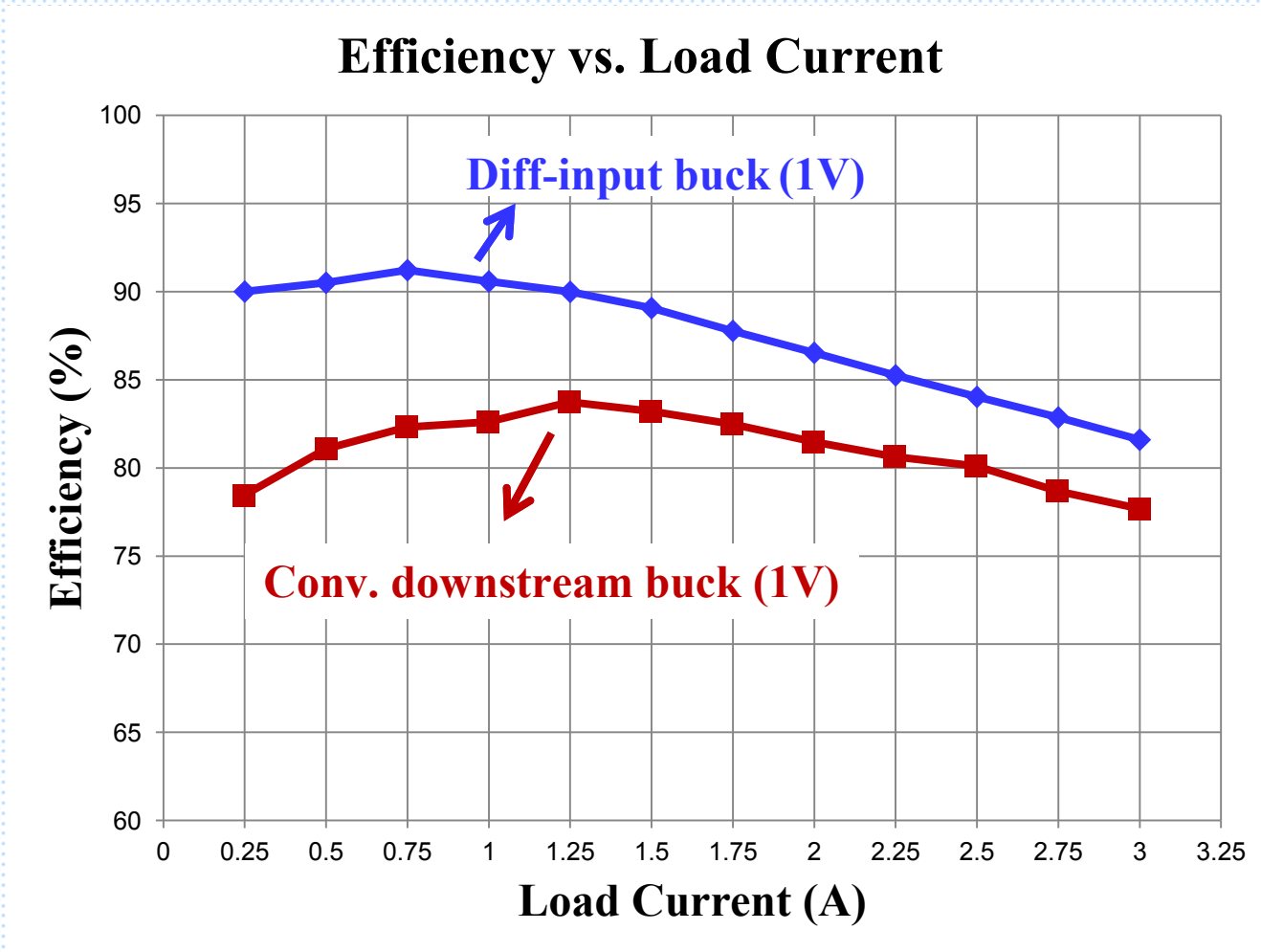
➤ Values in the table are normalized with respect to the conventional architecture (left fig)

	V_{sw_norm}	L_{norm}	P_{sw_norm}	f_{sw_norm}
Diff-input buck 3.3 V	0.44	0.49	0.44	1
Diff-input buck 1 V	0.44	0.68	0.44	1
Diff-input buck 3.3 V (incr. f_{sw})	0.44	0.25	0.88	2
Diff-input buck 1 V (incr. f_{sw})	0.44	0.34	0.88	2

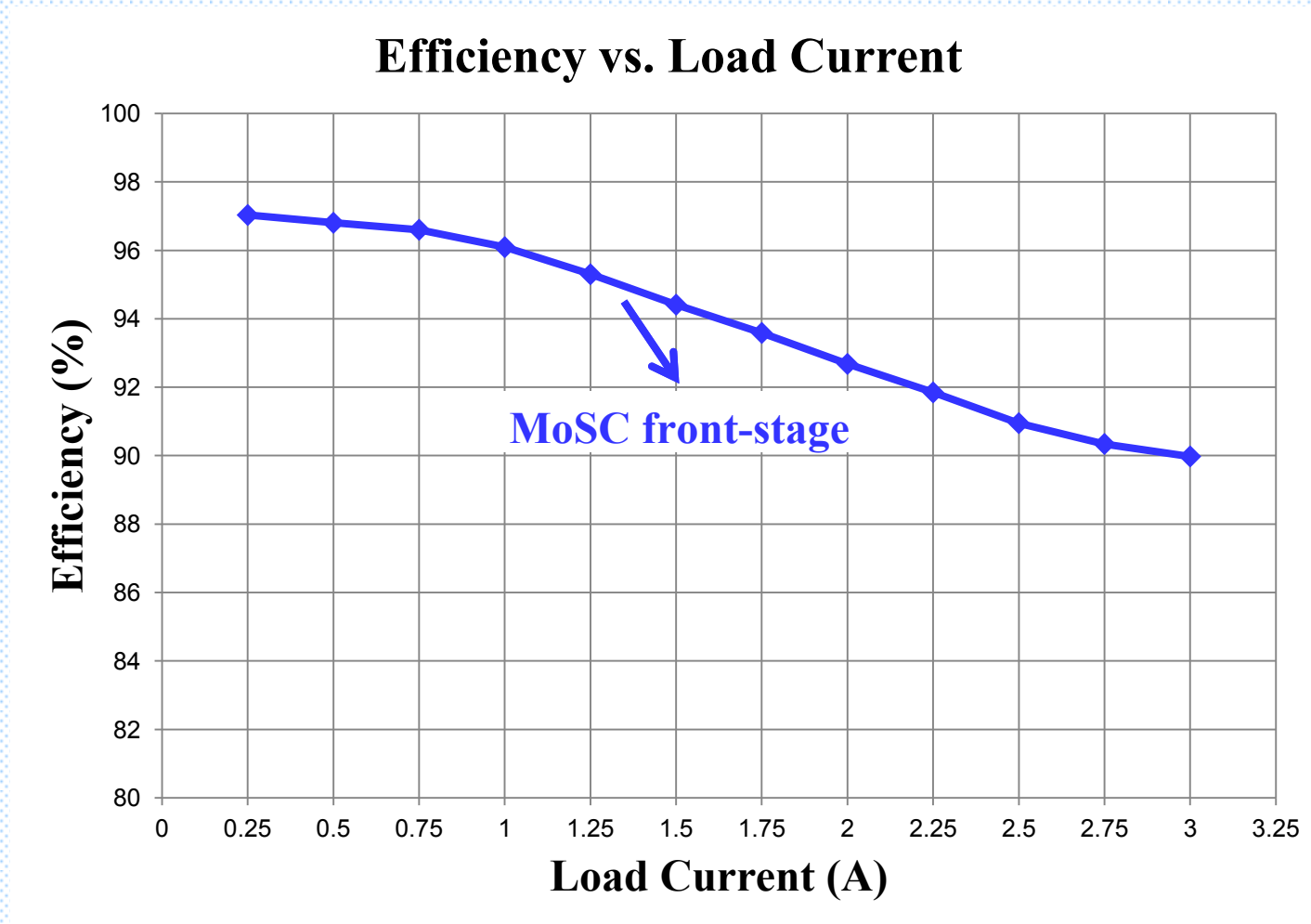
➤ 3.3 V buck converter: 50% ripple reduction



- 1 V buck converter: 12% improvement at lighter loads

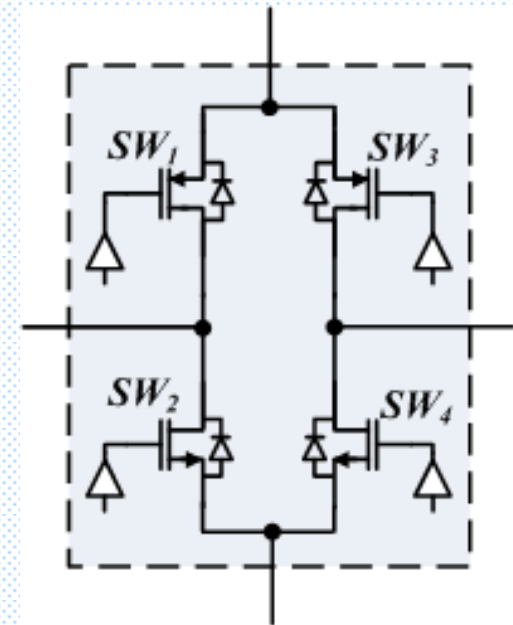
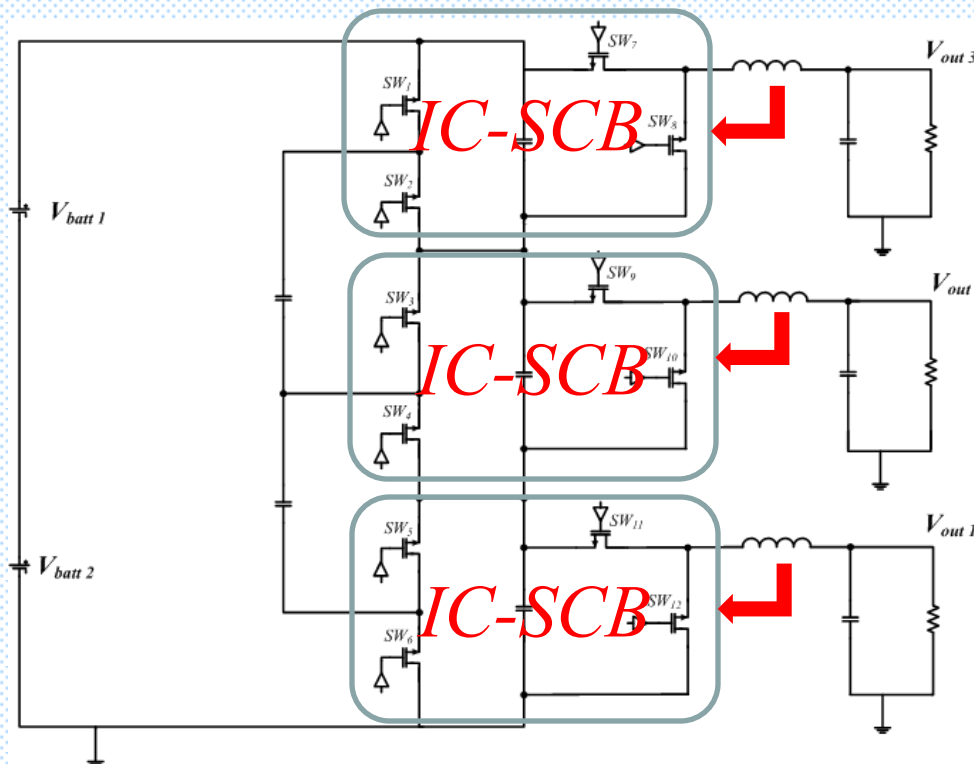


- MoSC front-end stage shows above 90% operating efficiency



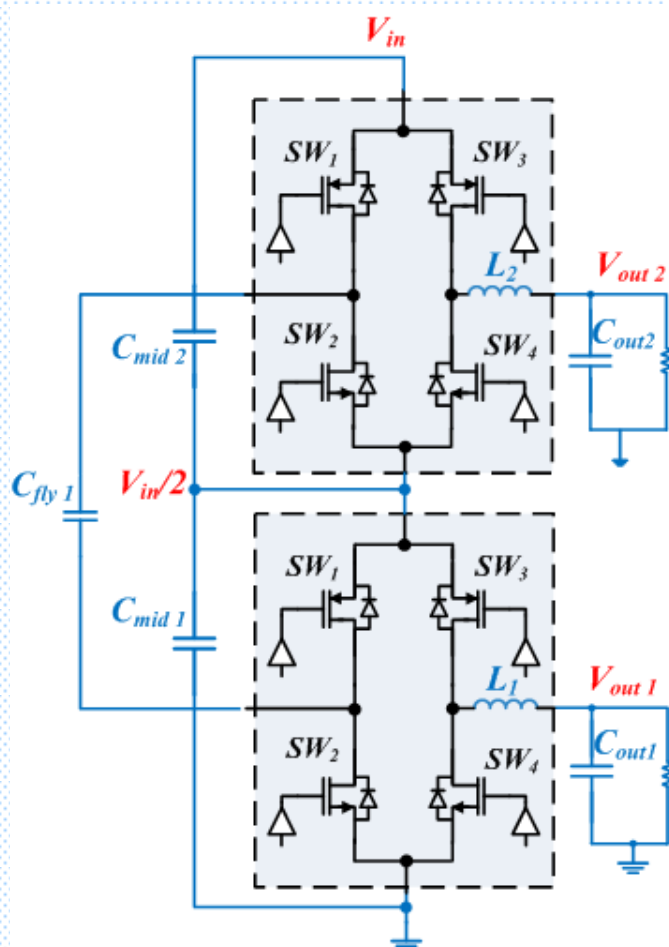
High Power Density Power Management IC Module

- Introduced architecture is symmetric and hence, multi-chip implementation allows modular design
- Power stage switches with gate drivers are integrated along with mixed-signal current programmed mode (CPM) compatibility
- On-chip inductors are later packaged together to provide low-volume high density power management solution

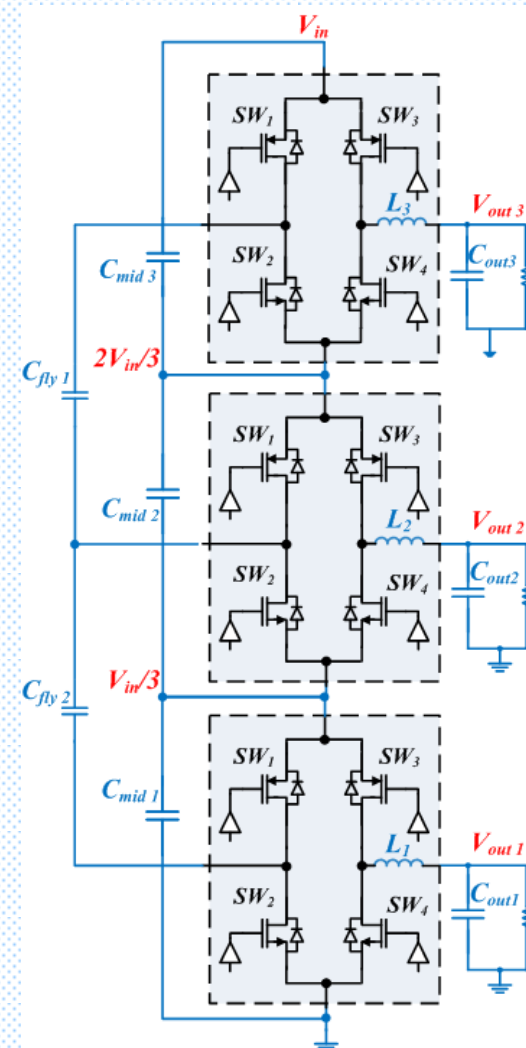


IC-Switched Cap Buck (SCB)

- Designed IC can be stacked-up to provide multiple output voltages and/or to allow higher input voltages

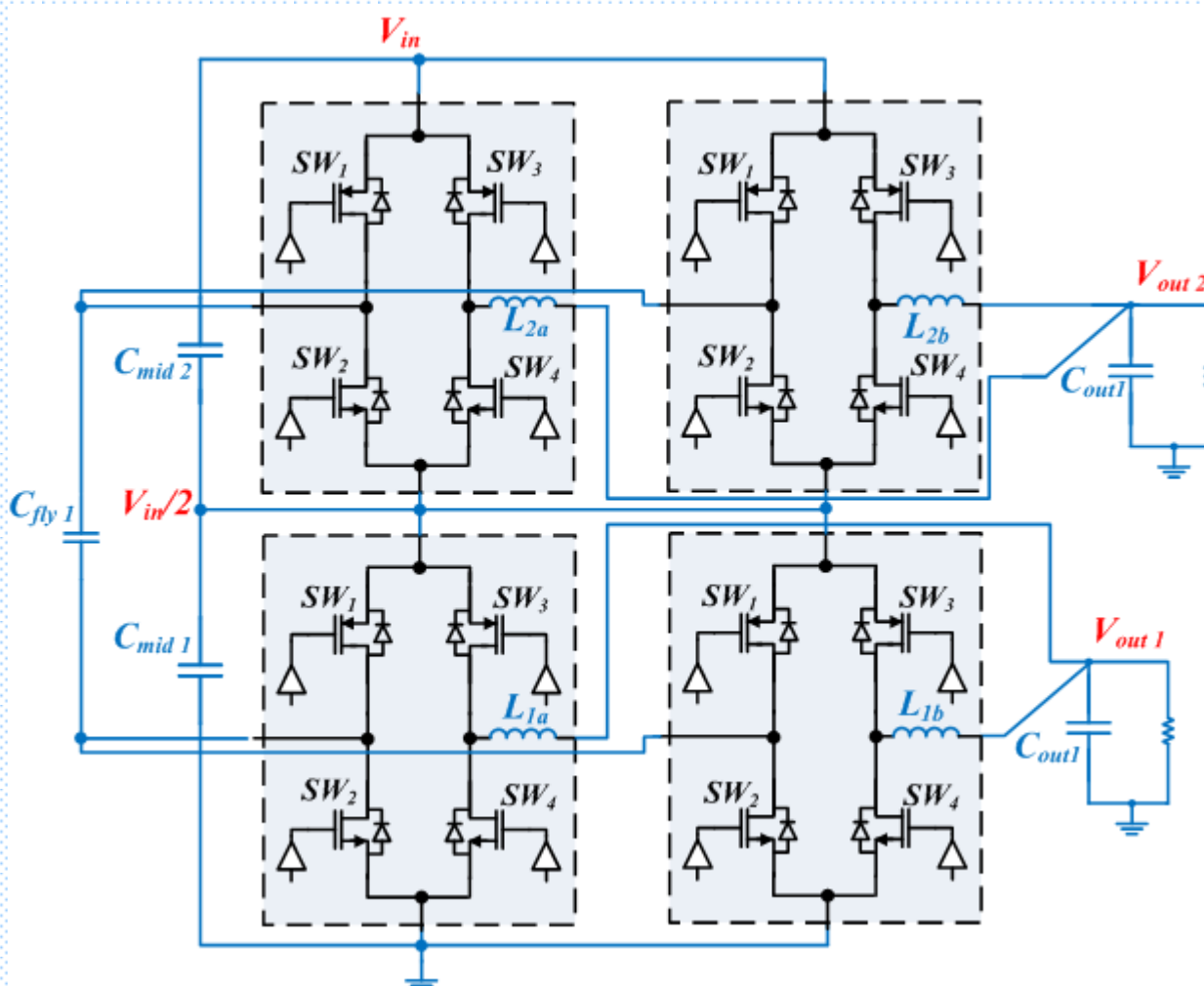


2-IC Solution



3-IC Solution

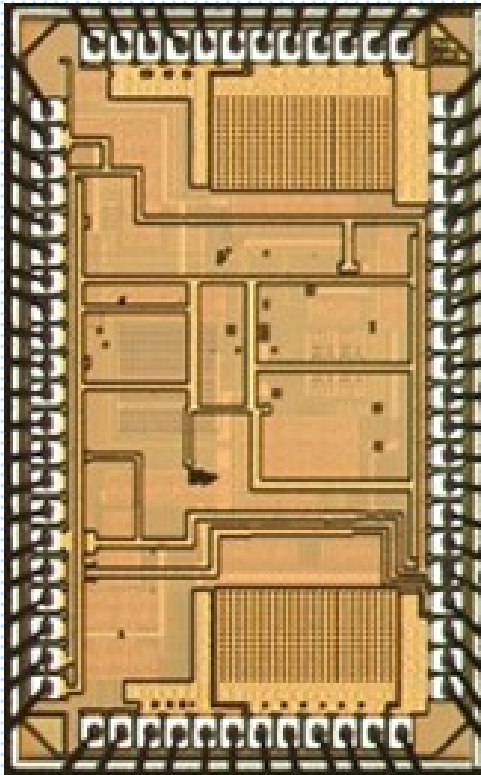
- ICs can also be connected in parallel to provide higher load current.



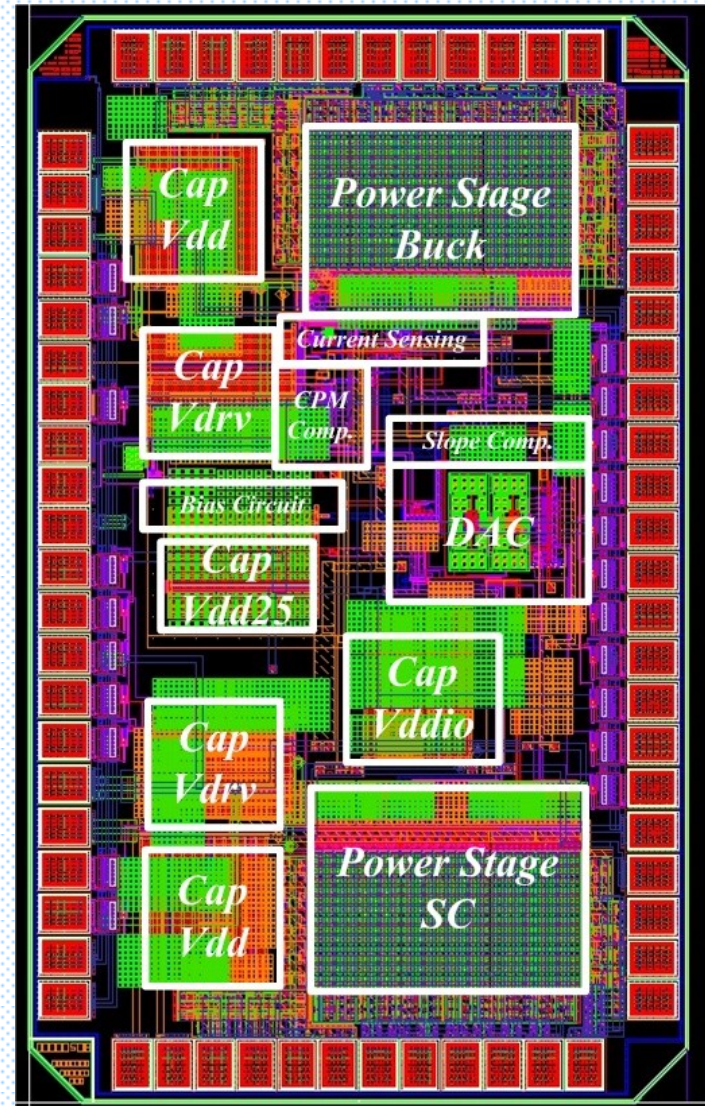
Test Chip (IC-SCB)



- ❑ Total Area: 1.5 mm X 2.5 mm
- ❑ 0.13 micron Tech.
- ❑ 1.2V FETs (thin oxide)
- ❑ 2.5V FETs (thick oxide)

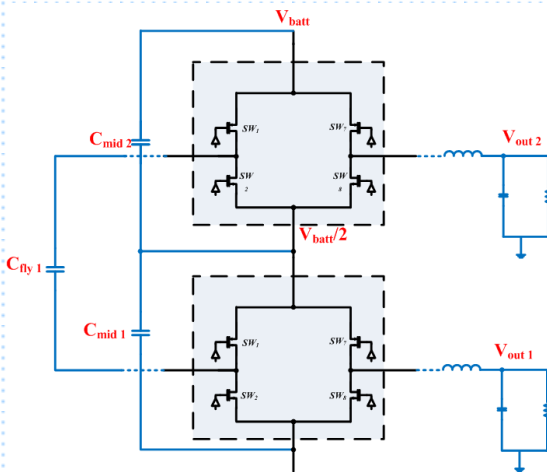


Die Photo

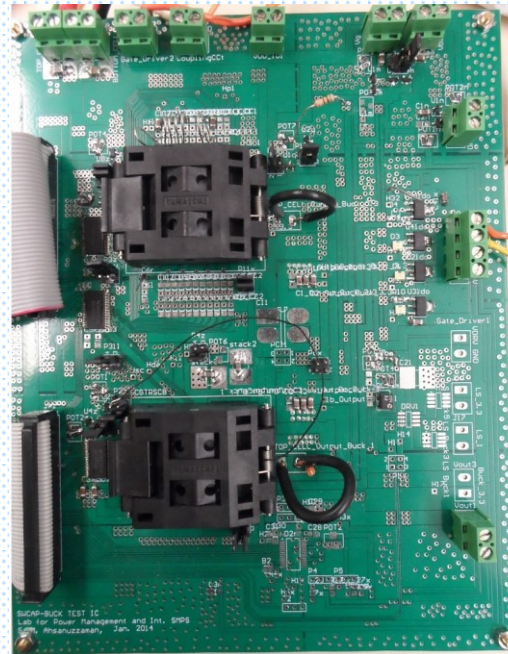


IC Layout

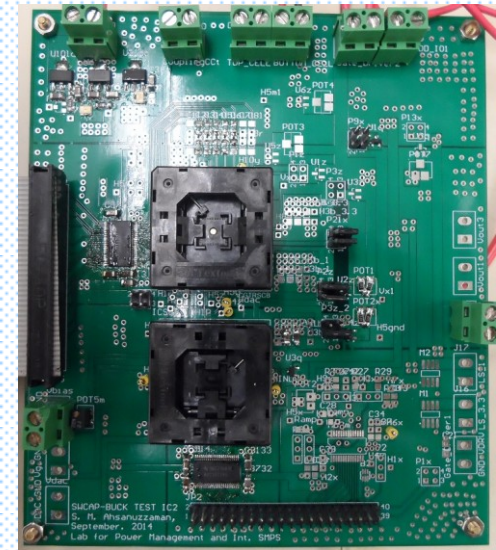
- 2 stacked IC-SCBs are tested for the proper system operation



Specifications	Value	Units
f_{sw_sc}	580	KHz
f_{sw_buck}	10	MHz
V_{in}	3	V
V_{out1}, V_{out2}	1, 2.5	V
Buck L, C	100, 10	nH, μ F
$R_{on} P_{mos}, N_{mos}$	150, 125	m Ω



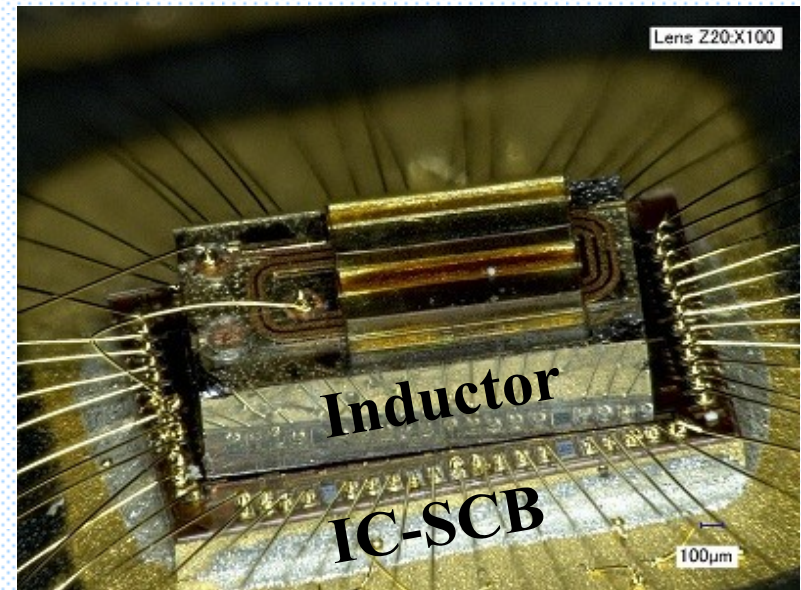
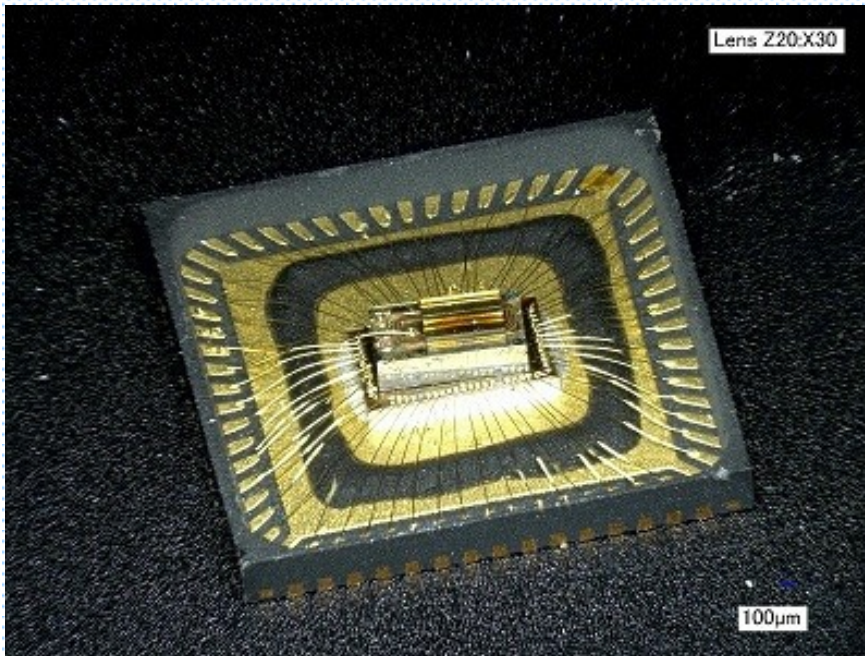
Test Board #1
(discrete inductors)



Test Board #2
(on-chip inductors)

□ Bonding picture: 1-IC

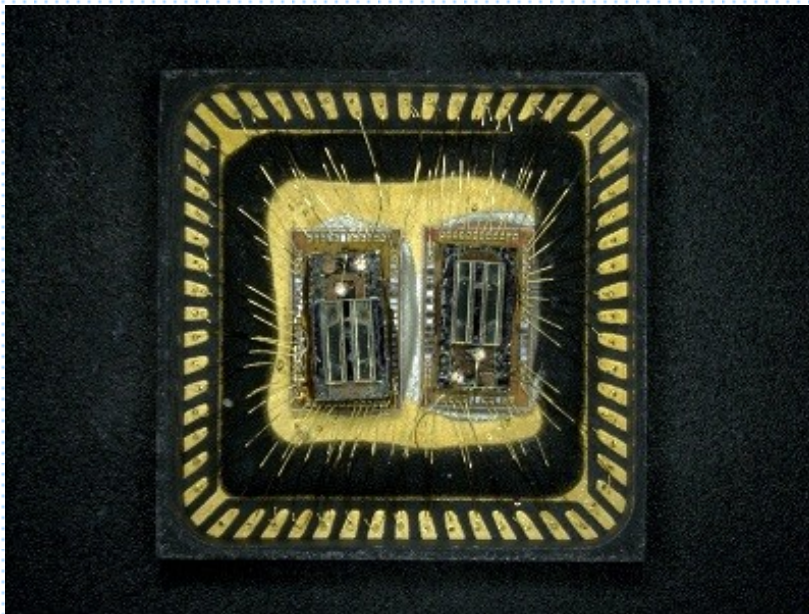
- Inductor (0603) is placed on top of the IC (1.5mm X 2.5mm)
- 60 QFN Package: 7mm X 7mm



Zoomed

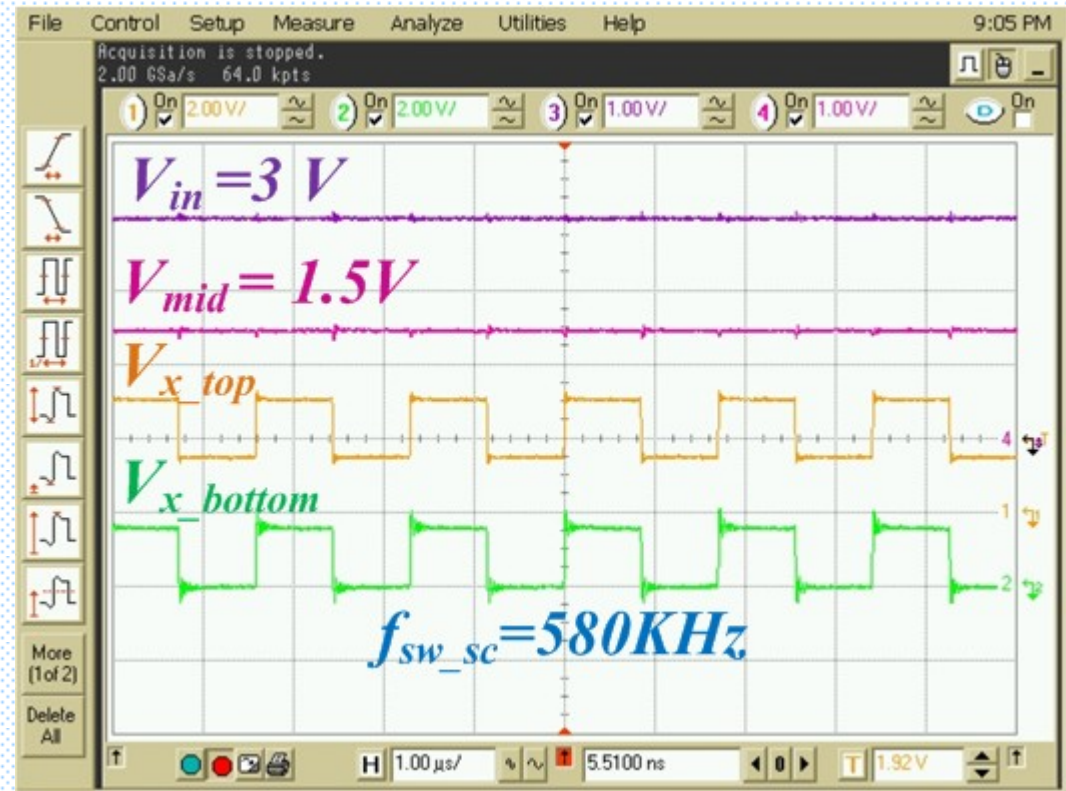
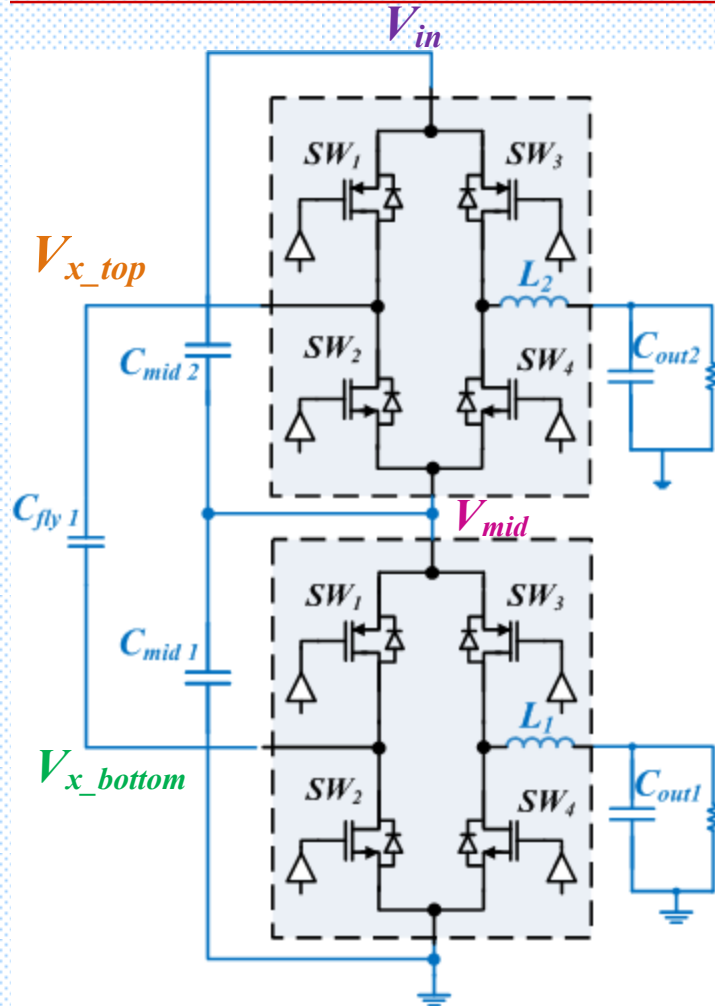
Size	Frequency	Target Inductance	Turn number	Width	Length	Core length	Rdc	Eff.
"0603" - -2	25 MHz	130 nH	4	686	1728	1150	0.269	89.65

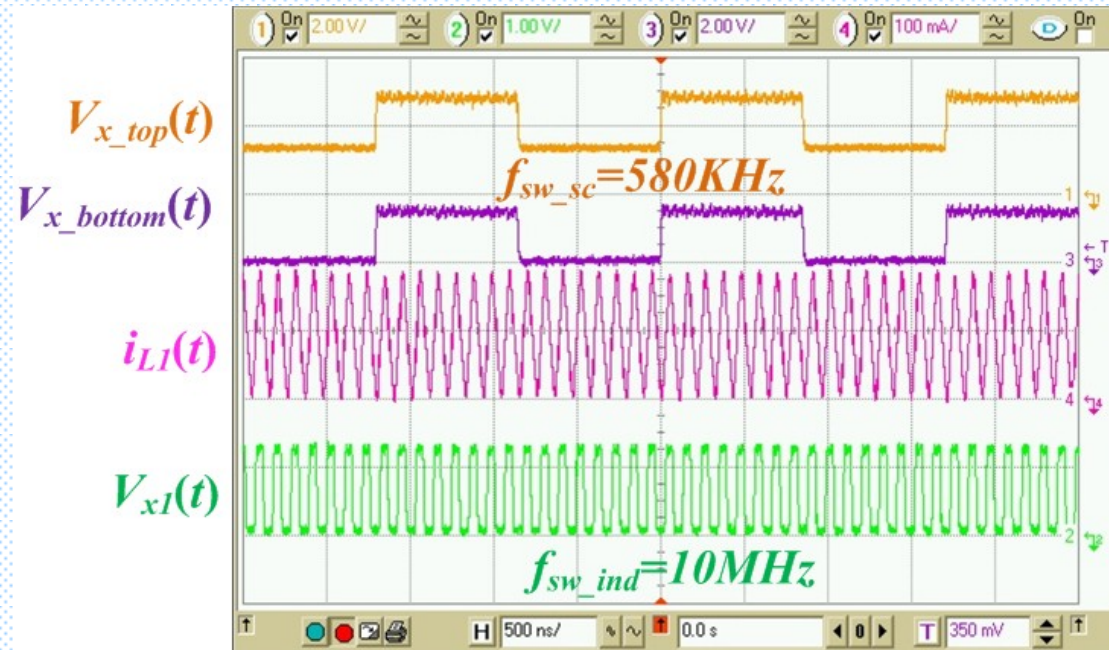
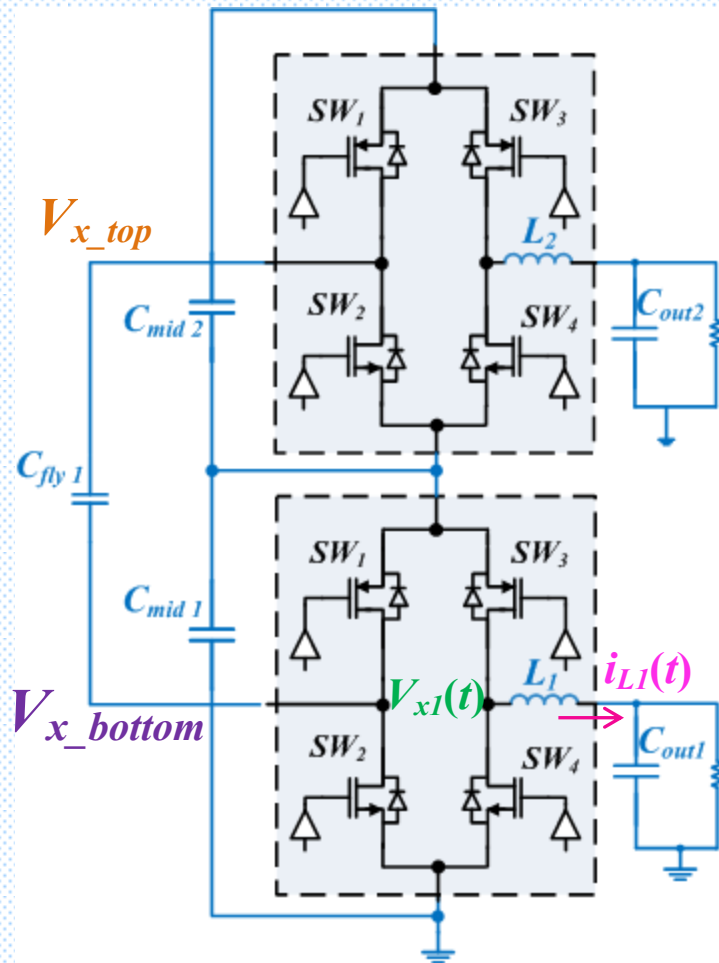
- ❑ Bonding picture: 2-ICs
 - Inductors (0603) are placed on top of the ICs (1.5mm X 2.5mm)
 - 60 QFN Package: 7mm X 7mm

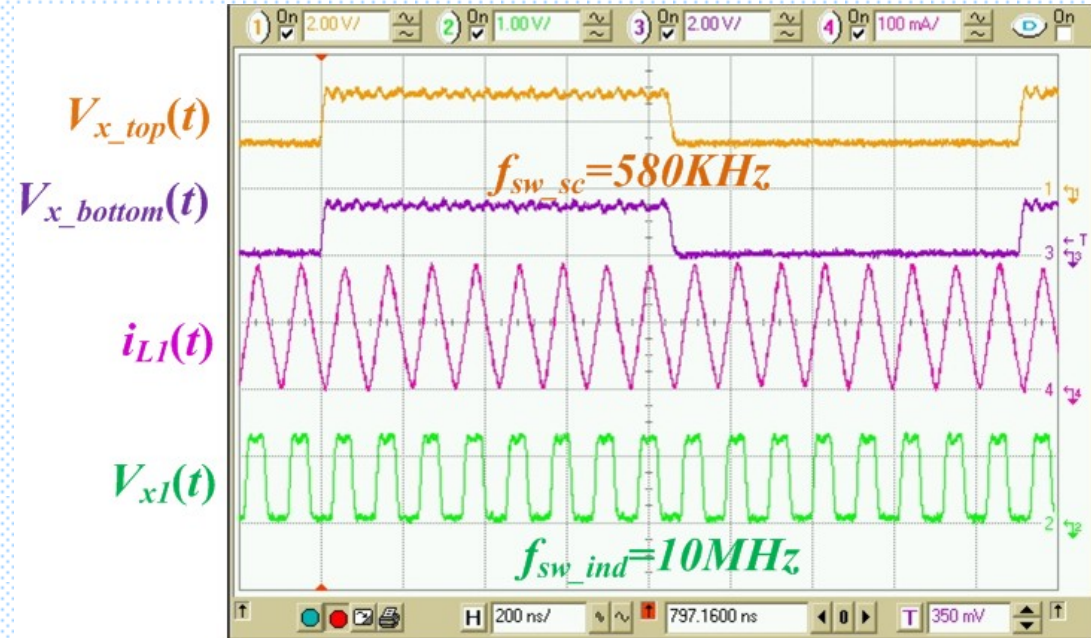
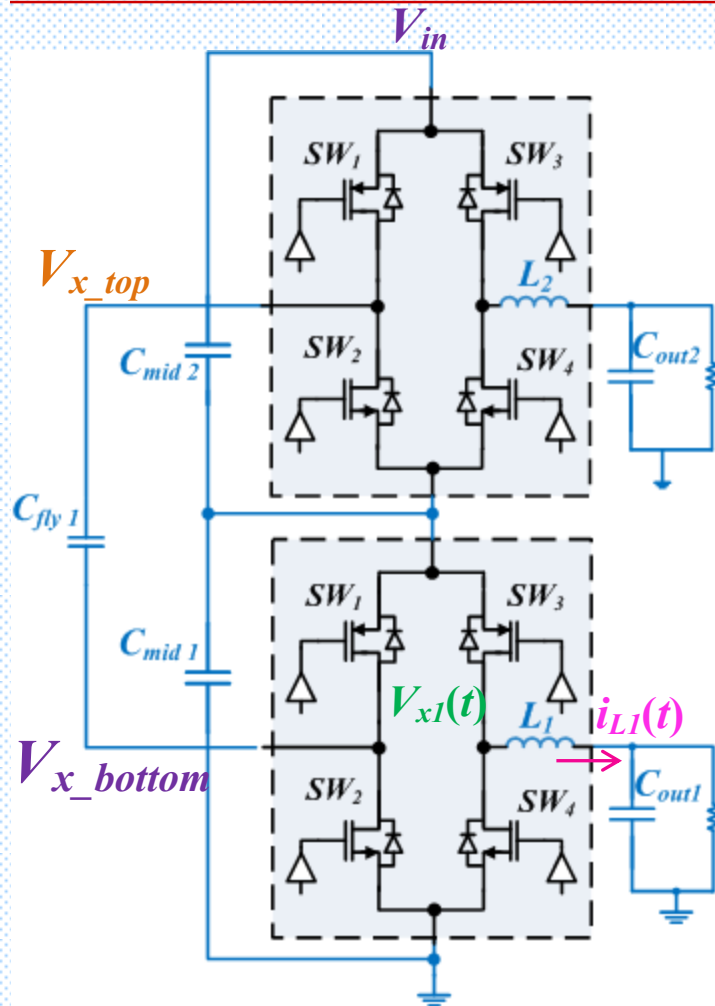


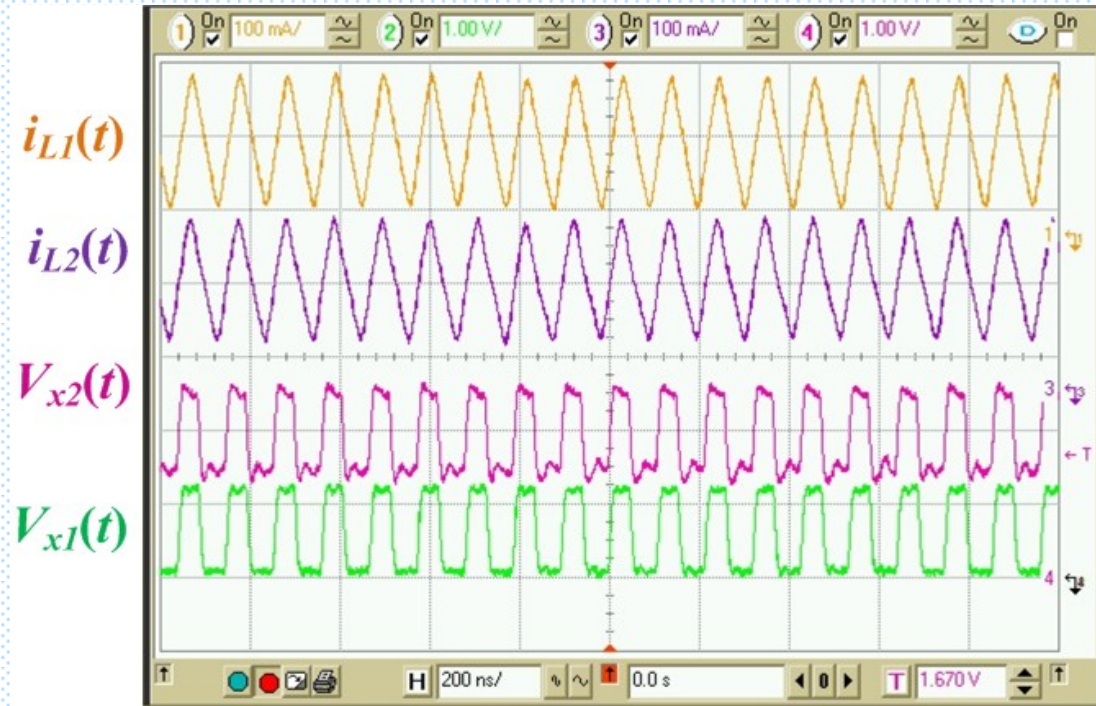
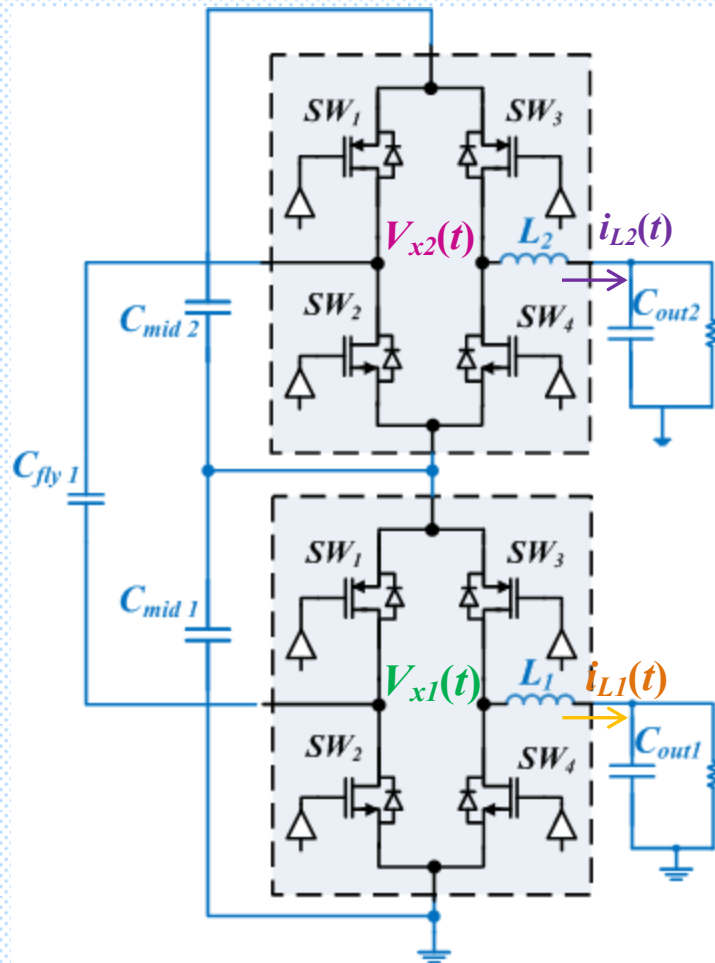
Zoomed

Size	Frequency	Target Inductance	Turn number	Width	Length	Core length	Rdc	Eff.
"0603" - -2	25 MHz	130 nH	4	686	1728	1150	0.269	89.65









- ❑ Introduced a high power density hybrid power management IC where:
 - SC voltage divider allows reducing voltage swings at the switching nodes of the inductor based differentially-connected stages
 - Reduces inductor volume without the need for significantly increasing switching frequency
 - Modular design allows easy adoption for multiple applications
 - Packaging the silicon dies with inductors shows an increased level of on-chip integration of the power management architectures
 - Future work will be focused on designing PMICs with on-chip inductors on the same die

Acknowledgement

The authors would like to acknowledge **Giovanni Garcea** and **Francesco Carobolante** from **Qualcomm Inc.** for their support and advice throughout the development of the power management modules.

We would also like to acknowledge **Ken Rodgers** and **Finbarr Waldron** from Packaging Group - **Tyndall** National Institute for package assembly and **Enterprise Ireland** for funding the inductor development.

Thank You